



PATENT
Customer No. 22,852
Attorney Docket No. 02887.0141-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Yukihito OOWAKI et al.) Group Art Unit: 2814
)
Application No.: 09/879,208) Examiner: S. Rao
)
Filed: June 13, 2001)
)
For: MIS TRANSISTOR AND METHOD)
FOR PRODUCING THE SAME)

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action of January 23, 2003, the period for reply to which extends through April 23, 2003, please amend this application as follows:

IN THE CLAIMS:

Please amend claims 14, 18, 22, and 27, as follows:

14. (Twice Amended) A method for producing a MIS transistor comprising a semiconductor substrate, source/drain regions formed on the semiconductor substrate, and a gate electrode provided above a channel region between the source/drain regions, said method comprising:

selectively forming a first film on said semiconductor substrate;

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